

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No. 070050.2717	Serial No. 10/525,297
	Applicant James S. Im	
	Filing Date 2/15/2005	Group 2811 2822
	Examiner Bac H. Au	

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
/BA/	1.	WO 0197266	12/20/2001	Mitsubishi Denki Kabushiki Kaisha
/BA/	2.	WO 0171791	09/27/2001	The Trustees of Columbia University In The City of New York

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Examiner	/Bac Au/	Date Considered	07/31/2007

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10/525297
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PTO/SB/08A (08-03)

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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet	1	of	1
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Complete if Known

Application Number	Not yet assigned 10/525297
Filing Date	Herewith 2/15/2005
First Named Inventor	James S. Im
Art Unit	Not yet assigned 2822
Examiner Name	Not yet assigned Bac H. Au
Attorney Docket Number	A35413-PCT-USA (070050.2717)

U. S. PATENT DOCUMENTS

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	14	4940505	07/1990	Schachameyer et al.
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/BA/	32	5529951	06/1996	Noguchi et al.
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/BA/	49	6130455	10/10/2000	Yoshinouchi
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/BA/	81	6621044	09/01/2003	Jain et al.
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↓	129	6563077	05/13/2003	Im

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/BA/	130		6582827	06/24/2003	Im
/BA/	33		6830993	12/14/2004	Im et al.

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	100	11064883	03/05/1999	JP	<u>No</u>
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Exam Initial	No.	Document No.	Publication Date	Country	Translation Yes No
/BA/	105	9931719	06/24/1999	WO	No
	106	0014784	03/16/2000	WO	
	107	0118854	03/15/2001	WO	
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	119	04017382	02/26/2004	WO	
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/BA/	121		04017380	02/26/2004	WO		
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